

STK17TA8

nvTime[™] Event Data Recorder 128K x 8 *AutoStore*[™] nvSRAM With Real-Time Clock

FEATURES

- Data Integrity of Simtek nvSRAM Combined with Full-Featured Real-Time Clock
- Watchdog Timer
- Clock Alarm with programmable Interrupts
- Capacitor or battery backup for RTC
- 25ns, 35ns and 45ns Access Times
- "Hands-off" Automatic STORE on Power Down with only a small capacitor
- STORE to QuantumTrap™ Initiated by Software, device pin, or on Power Down
- RECALL to SRAM Initiated by Software or Power Up
- Unlimited READ, WRITE and RECALL Cycles
- High-reliability
 - o Endurance to 500K Cycles
 - o Retention to 100 years at 125 °C
- 10mA Typical I_{CC} at 200ns Cycle Time
- Single 3V +20%, -10% Operation
- SSOP Package, ROHS compliant

DESCRIPTION

The Simtek STK17TA8 combines a 1 Mbit nonvolatile static RAM with a full-featured real-time clock in a reliable, monolithic integrated circuit. The embedded nonvolatile elements incorporate Simtek's *QuantumTrap™* technology producing the world's most reliable nonvolatile memory. The SRAM can be read and written an unlimited number of times, while independent, nonvolatile data resides in the nonvolatile elements.

The Real-Time Clock function provides an accurate clock with leap year tracking and a programmable, high accuracy oscillator. The Alarm function is programmable for one-time alarms or periodic seconds, minutes, hours, or days. There is also a programmable Watchdog Timer for process control.

BLOCK DIAGRAM

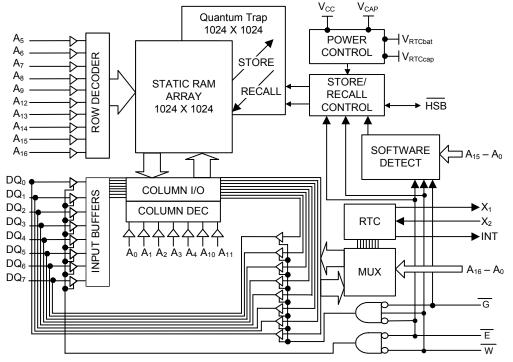
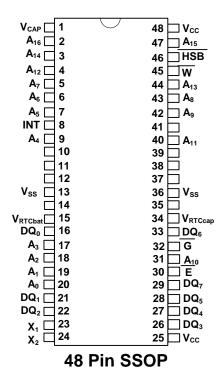


Figure 1. Block Diagram

PACKAGES





Approximate PCB area usage. See website for detailed package size specifications.

PIN DESCRIPTIONS

Pin Name	I/O	Description
A ₁₆ - A ₀	Input	Address: The 17 address inputs select one of 131,056 bytes in the nvSRAM array or one of 16 bytes in the clock register map.
DQ ₇ –DQ ₀	I/O	Data: Bi-directional 8-bit data bus for accessing the nvSRAM array and RTC.
E	Input	Chip Enable: The active low E input selects the device.
W	Input	Write Enable: The active low W enables data on the DQ pins to be written to the address location latched by the falling edge of E .
G	Input	Output Enable: The active low \overline{G} input enables the data output buffers during read cycles. De-asserting \overline{G} high causes the DQ pins to tri-state.
X ₁	Output	Crystal Connection, drives crystal on startup.
X_2	Input	Crystal Connection for 32.768 kHz crystal.
V _{RTCcap}	Power Supply	Capacitor supplied backup RTC supply voltage. (Left unconnected if V _{RTCbat} is used.)
V _{RTCbat}	Power Supply	Battery supplied backup RTC supply voltage. (Left unconnected if VRTCcap is used.)
V _{CC}	Power Supply	Power 3.0V +20%, -10%
HSB	I/O	Hardware Store Busy: When low this output indicates a Hardware Store is in progress. When pulled low external to the chip it will initiate a nonvolatile STORE operation. A weak internal pull up resistor keeps this pin high if not connected. (Connection Optional)
INT	Output	Interrupt Output: Can be programmed to respond to the clock alarm, the watchdog timer and the power monitor. Programmable to either active high (push/pull) or active low (open-drain).
V _{CAP}	Power Supply	Autostore Capacitor: Supplies power to nvSRAM during power loss to store data from SRAM to nonvolatile elements.
V_{SS}	Power Supply	Ground
(Blank)	No Connect	Unlabeled pins have no internal connection.

ABSOLUTE MAXIMUM RATINGS^a

DC Output Current (1 output at a time, 1s duration)

 $\begin{array}{lll} \mbox{Power Supply Voltage} & -0.5\mbox{V to } +4.1\mbox{V} \\ \mbox{Voltage on Input Relative to V}_{SS} & -0.5\mbox{V to } (\mbox{V}_{CC} + 0.5\mbox{V}) \\ \mbox{Voltage on Outputs} & -0.5\mbox{V to } (\mbox{V}_{CC} + 0.5\mbox{V}) \\ \mbox{Temperature under Bias} & -55\mbox{°C to } 125\mbox{°C} \\ \mbox{Junction Temperature} & -55\mbox{°C to } 140\mbox{°C} \\ \mbox{Storage Temperature} & -65\mbox{°C to } 150\mbox{°C} \\ \mbox{Power Dissipation} & 1\mbox{W} \\ \end{array}$

Notes

a: Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Package Thermal Characteristics see website: http://www.simtek.com/

DC CHARACTERISTICS

		Comn	nercial	Indu	strial		
Symbol	Parameter	MIN	MAX	MIN	MAX	Units	Notes
I _{CC1}	Average V _{CC} Current		65 55 50		70 60 55	mA mA mA	$\begin{split} &t_{\text{AVAV}} = 25\text{ns} \\ &t_{\text{AVAV}} = 35\text{ns} \\ &t_{\text{AVAV}} = 45\text{ns} \\ &\text{Dependent on output loading and cycle} \\ &\text{rate. Values obtained without output loads.} \end{split}$
I _{CC2}	Average V _{CC} Current during STORE		3		3	mA	All Inputs Don't Care, V_{CC} = max Average current for duration of STORE cycle (t_{STORE}).
I _{CC3}	Average V _{CC} Current at t _{AVAV} = 200ns 3V, 25°C, Typical		10		10	mA	W ≥ (V _{CC} – 0.2V) All Others Inputs Cycling, at CMOS Levels. Dependent on output loading and cycle rate. Values obtained without output loads.
I _{CC4}	Average V _{CAP} Current during AutoStore™ Cycle		3		3	mA	All Inputs Don't Care Average current for duration of STORE cycle (t _{STORE}).
I _{SB}	V _{CC} Standby Current (Standby, Stable CMOS Input Levels)		3		3	mA	$\overline{E} \ge (V_{CC} - 0.2V)$ All Others $V_{IN} \le 0.2V$ or $\ge (V_{CC} - 0.2V)$ Standby current level after nonvolatile cycle is complete.
I _{ILK}	Input Leakage Current		±1		±1	μA	V _{CC} = max V _{IN} = V _{SS} to V _{CC} V _{CC} = max
I _{OLK}	Off-State Output Leakage Current		±1		±1	μA	$V_{CC} = max$ $V_{IN} = V_{SS} \text{ to } V_{CC}, \overline{E} \text{or } \overline{G} \geq V_{IH}$
V_{IH}	Input Logic "1" Voltage	2.0	V _{CC} + 0.3	2.0	V _{CC} + 0.3	V	All Inputs
V_{IL}	Input Logic "0" Voltage	V _{SS} – 0.5	0.8	V _{SS} – 0.5	0.8	V	All Inputs
V_{OH}	Output Logic "1" Voltage	2.4		2.4		V	I _{OUT} = -2mA
V_{OL}	Output Logic "0" Voltage		0.4		0.4	V	I _{OUT} = 4mA
T _A	Operating Temperature	0	70	-40	85	°C	
V_{CC}	Operating Voltage	2.7	3.6	2.7	3.6	V	3.0V +20%, -10%
V_{CAP}	Storage Capacitor	17	57	17	57	μF	Between Vcap pin and Vss, 5V rated.

15mA

AC TEST CONDITIONS

Input Pulse Levels		0V to 3V
Input Rise and Fall Times		≤ 5ns
Input and Output Timing Re	eference Levels	1.5V
Output Load	See Figure 2 a	and Figure 3

CAPACITANCE^b

SYMBOL	PARAMETER	PARAMETER MAX		CONDITIONS
C _{IN}	Input Capacitance	7	pF	$\Delta V = 0$ to 3V
C _{OUT}	Output Capacitance	7	pF	$\Delta V = 0$ to 3V

Notes

b: These parameters are guaranteed but not tested

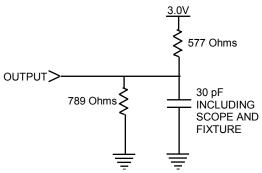


Figure 2. AC Output Loading

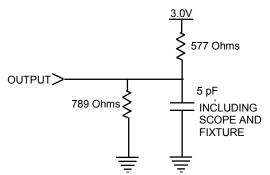
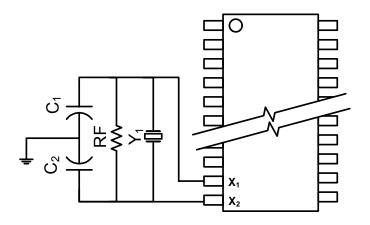


Figure 3. AC Output Loading, for tristate specs ($t_{HZ},\,t_{LZ},\,t_{WLQZ},\,t_{WHQZ},\,t_{GLQX},\,t_{GHQZ}$)

RTC DC CHARACTERISTICS

Symbol	Parameter	Comn	Commercial		strial	Units	Notes
Syllibol	Farameter	MIN	MAX	MIN	MAX	Ullits	Notes
I _{BAK}	RTC Backup Current	-	300	-	350	nA	From either V _{RTCcap} or V _{RTCbat}
V _{RTCbat}	RTC Battery Pin Voltage	1.8	3.3	1.8	3.3	V	Typical = 3.0 Volts during normal operation
V _{RTCcap}	RTC Capacitor Pin Voltage	1.2	2.7	1.2	2.7	V	Typical = 2.4 Volts during normal operation
toscs	RTC Oscillator time to start	-	10	•	10	sec	@ MIN Temperature from Power up or Enable
-0303	The second secon	-	5	-	5	sec	@25°C from Power up or Enable

RTC RECOMMENDED COMPONENT CONFIGURATION



Recommended Values

 $Y_1 = 32.768 \text{ KHz}$ RF = 10M Ohm $C_1 = 0$

 $C_2 = 56 pF$

Figure 4. RTC COMPONENT CONFIGURATION

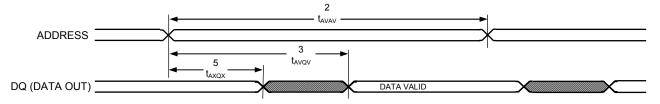
SRAM READ CYCLES #1 & #2

NO.		SYMBO	LS	PARAMETER _	STK17	TA8-25	STK17	TA8-35	STK17TA8-45		UNITS
	#1	#2	Alt.		MIN	MAX	MIN	MAX	MIN	MAX	
1		t _{ELQV}	t _{ACS}	Chip Enable Access Time		25		35		45	ns
2	t _{AVAV} c	t _{AVAV} ^c	t _{RC}	Read Cycle Time	25	25			45		ns
3	$t_{\text{AVQV}}^{\text{d}}$		t _{AA}	Address Access Time		25		35		45	ns
4		t_{GLQV}	t _{OE}	Output Enable to Data Valid		12		15		20	ns
5	t_{AXQX}^{d}		t _{OH}	Output Hold after Address Change	3		3		3		ns
6		t _{ELQX}	t _{LZ}	Chip Enable to Output Active	3		3		3		ns
7		t _{EHQZ} e	t_{HZ}	Chip Disable to Output Inactive		10		13		15	ns
8		t_{GLQX}	t _{OLZ}	Output Enable to Output Active	0		0		0		ns
9		t _{GHQZ} e	t _{OHZ}	Output Disable to Output Inactive		10		13		15	ns
10		t _{ELICC} ^b	t _{PA}	Chip Enable to Power Active	0		0		0		ns
11		t _{EHICC} ^b	t _{PS}	Chip Disable to Power Standby		25		35		45	ns

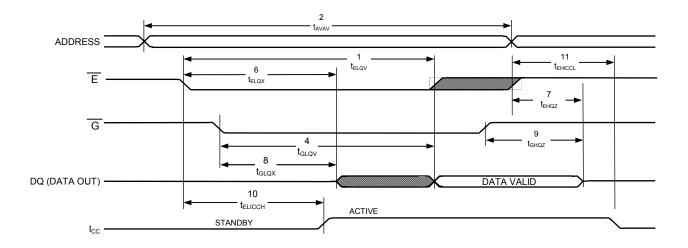
Notes

- c: W must be high during SRAM READ cycles
- d: Device is continuously selected with \overline{E} and \overline{G} both low
- e: Measured \pm 200mV from steady state output voltage
- f: HSB must remain high during READ and WRITE cycles.

SRAM READ CYCLE #1: Address Controlled c,d,f



SRAM READ CYCLE #2: E Controlled^{c,f}



SRAM WRITE CYCLES #1 & #2

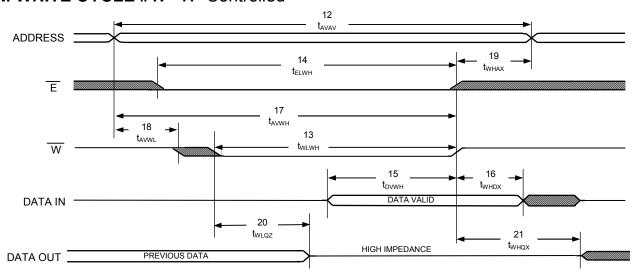
NO.	;	SYMBOLS		PARAMETER	STK17	ΓA8-25	STK17TA8-35		STK17TA8-45		UNITS
NO.	#1	#2	Alt.	PARAMETER	MIN	MAX	MIN	MAX	MIN	MAX	
12	t _{AVAV}	t _{AVAV}	t _{wc}	Write Cycle Time	25		35		45		ns
13	t _{wLWH}	t _{WLEH}	t _{WP}	Write Pulse Width	20		25		30		ns
14	t _{ELWH}	t _{ELEH}	t _{CW}	Chip Enable to End of Write	20		25		30		ns
15	t _{DVWH}	t _{DVEH}	t _{DW}	Data Set-up to End of Write	10		12		15		ns
16	t _{WHDX}	t _{EHDX}	t _{DH}	Data Hold after End of Write	0		0		0		ns
17	t _{AVWH}	t _{AVEH}	t _{AW}	Address Set-up to End of Write	20		25		30		ns
18	t _{AVWL}	t _{AVEL}	t _{AS}	Address Set-up to Start of Write	0		0		0		ns
19	t _{WHAX}	t _{EHAX}	t _{WR}	Address Hold after End of Write	0		0		0		ns
20	t _{WLQZ} e,g		t _{wz}	Write Enable to Output Disable		10		13		15	ns
21	t _{WHQX}		tow	Output Active after End of Write	3		3		3		ns

Notes

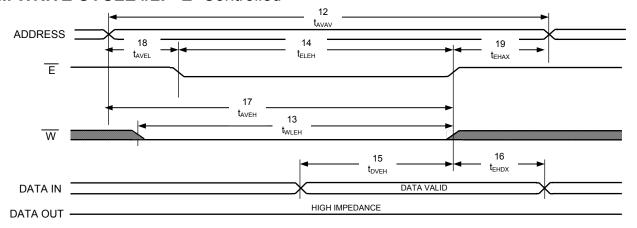
g: If \overline{W} is low when \overline{E} goes low, the outputs remain in the high-impedance state.

h: \overline{E} or \overline{W} must be $\geq V_{IH}$ during address transitions.

SRAM WRITE CYCLE #1: W Controlled^{h,f}



SRAM WRITE CYCLE #2: E Controlled^{h,f}

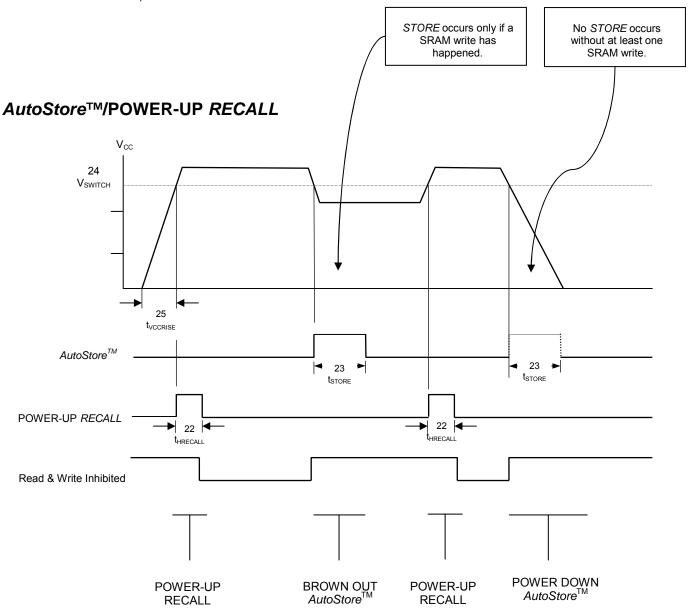


AutoStore™ /POWER-UP RECALL

NO.	SYMBO	DLS	PARAMETER	STK1	7TA8	UNITS	NOTES
NO.	Standard	Alternate		MIN	MAX	UNITS	NOTES
22	t _{HRECALL}		Power-up RECALL Duration		20	ms	i
23	t _{STORE}	t _{HLHZ}	STORE Cycle Duration		12.5	ms	j,k
24	V _{SWITCH}		Low Voltage Trigger Level	2.55	2.65	٧	
25	t _{VCCRISE}		V _{CC} Rise Time	150		μs	

Notes

- i: t_{HRECALL} starts from the time V_{CC} rises above V_{SWITCH} j: If an SRAM WRITE has not taken place since the last nonvolatile cycle, no STORE will take place k: Industrial Grade Devices require 15ms MAX.



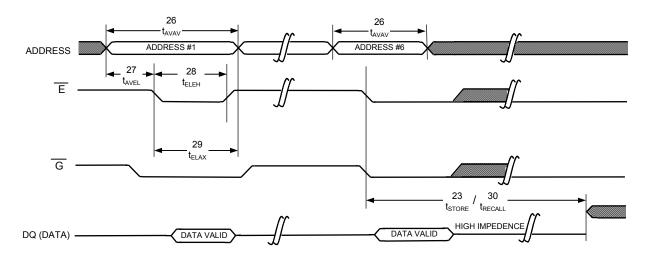
Note: Read and Write cycles will be ignored during STORE, RECALL and while V_{CC} is below V_{SWITCH}

SOFTWARE-CONTROLLED STORE/RECALL CYCLE^{I,m}

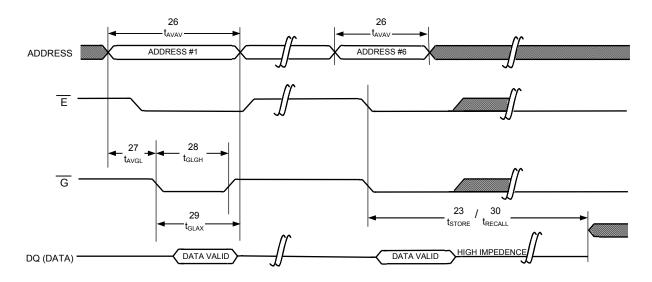
		SYMBOLS			STK17	TA8-25	STK17	TA8-35	STK17	TA8-45		
NO.	E	G	Alt.	PARAMETER	MIN	MAX	MIN	MAX	MIN	MAX	UNITS	NOTES
26	t _{AVAV}	t _{AVAV}	t _{RC}	STORE/RECALL Initiation Cycle Time	25		35		45		ns	m
27	t _{AVEL}	t _{AVGL}	t _{AS}	Address Set-up Time	0		0		0		ns	
28	t _{ELEH}	t _{GLGH}	t _{CW}	Clock Pulse Width	20		25		30		ns	
29	t _{ELAX}	t _{GLAX}		Address Hold Time	20		20		20		ns	
30	t _{RECALL}	t _{RECALL}		RECALL Duration		60		60		60	μs	

Notes

SOFTWARE STORE/RECALL CYCLE: E Controlled^m



SOFTWARE STORE/RECALL CYCLE: G Controlled^m



I: The software sequence is clocked with \overline{E} controlled READs or \overline{G} controlled READs.

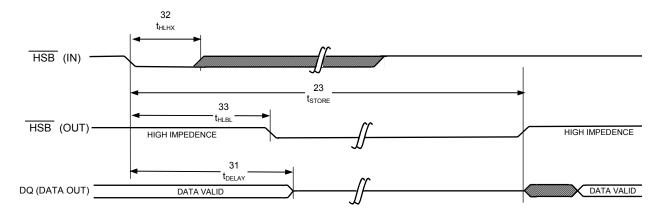
m: The six consecutive addresses must be read in the order listed in the Mode Selection Table. W must be high during all six consecutive cycles.

HARDWARE STORE CYCLE

NO.	SYMB	OLS	PARAMETER	STK	17TA8	UNITS	NOTES
NO.	NO. Standard A		FARAINETER	MIN	MAX	UNITS	NOTES
31	t _{DELAY}	t _{HLQZ}	Time Allowed to Complete SRAM Cycle	1		μs	n
32	t _{HLHX}		Hardware STORE Pulse Width	15		ns	
33	t _{HLBL}		Hardware STORE Low to STORE Busy		300	ns	

Notes

HARDWARE STORE CYCLE



n: Read and Write cycles in progress before HSB is asserted are given this amount of time to complete.

MODE SELECTION

Ē	w	G	A ₁₅ - A ₀	MODE	I/O	POWER	NOTES
Н	Х	Х	Х	Not Selected	Output High Z	Standby	
L	Н	L	Х	Read SRAM	Output Data	Active	
L	L	Х	Х	Write SRAM	Input Data	Active	
L	н	L	0x4E38 0xB1C7 0x83E0 0x7C1F 0x703F 0x8FC0	Read SRAM Read SRAM Read SRAM Read SRAM Read SRAM Nonvolatile Store	Output Data Output Data Output Data Output Data Output Data Output High Z	Active	o,p,q
L	Н	L	0x4E38 0xB1C7 0x83E0 0x7C1F 0x703F 0x4C63	Read SRAM Read SRAM Read SRAM Read SRAM Read SRAM Read SRAM Nonvolatile Recall	Output Data Output Data Output Data Output Data Output Data Output Data Output High Z	Active	p,q,o

Notes

o: The six consecutive addresses must be in the order listed. W must be high during all six consecutive cycles to enable a nonvolatile cycle.

p: While there are 17 addresses on the STK17TA8, only the lower 16 are used to control software modes

q: I/O state depends on the state of \overline{G} . The I/O table shown assumes \overline{G} low.

DEVICE OPERATION

nvSRAM

The STK17TA8 nvSRAM is made up of two functional components paired in the same physical cell. These are a SRAM memory cell and a nonvolatile QuantumTrap™ cell. The SRAM memory cell operates as a standard fast static RAM. Data in the SRAM can be transferred to the nonvolatile cell (the STORE operation), or from the nonvolatile cell to SRAM (the RECALL operation). This unique architecture allows all cells to be stored and recalled in parallel. During the STORE and RECALL operations SRAM READ and WRITE operations are inhibited. The STK17TA8 supports unlimited reads and writes just like a typical SRAM. In addition, it provides unlimited RECALL operations from the nonvolatile cells and up to 1 million STORE operations.

SRAM READ

The STK17TA8 performs a READ cycle whenever $\overline{\mathbb{E}}$ and $\overline{\mathbb{G}}$ are low while $\overline{\mathbb{W}}$ and $\overline{\mathbb{HSB}}$ are high. The address specified on pins $A_{16\text{-}0}$ determines which of the 131,056 data bytes will be accessed. When the READ is initiated by an address transition, the outputs will be valid after a delay of t_{AVQV} (READ cycle #1). If the READ is initiated by $\overline{\mathbb{E}}$ or $\overline{\mathbb{G}}$, the outputs will be valid at t_{ELQV} or at t_{GLQV} , whichever is later (READ cycle #2). The data outputs will repeatedly respond to address changes within the t_{AVQV} access time without the need for transitions on any control input pins, and will remain valid until another address change or until $\overline{\mathbb{E}}$ or $\overline{\mathbb{G}}$ is brought high, or $\overline{\mathbb{W}}$ or $\overline{\mathbb{HSB}}$ is brought low.

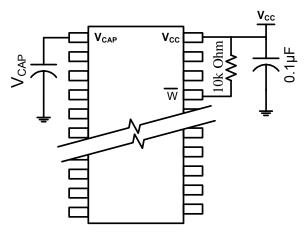


Figure 5: AutoStore[™] Mode

SRAM WRITE

A WRITE cycle is performed whenever \overline{E} and \overline{W} are low and \overline{HSB} is high. The address inputs must be stable prior to entering the WRITE cycle and must remain stable until either \overline{E} or \overline{W} goes high at the end of the cycle. The data on the common I/O pins DQ₀₋₇ will be written into the memory if it is valid t_{DVWH} before the end of a \overline{W} controlled WRITE or t_{DVEH} before the end of an \overline{E} controlled WRITE.

It is recommended that \overline{G} be kept high during the entire WRITE cycle to avoid data bus contention on common I/O lines. If \overline{G} is left low, internal circuitry will turn off the output buffers t_{WLQZ} after \overline{W} goes low.

AutoStore™ OPERATION

The STK17TA8 stores data to nvSRAM using one of three storage operations. These three operations are Hardware Store, activated by $\overline{\mbox{HSB}}$, Software Store, actived by an address sequence, and $AutoStore^{\mbox{\tiny TM}}$, on device power down.

AutoStore™ operation is a unique feature of Simtek QuantumTrap™ technology and is enabled by default on the STK17TA8.

During normal operation, the device will draw current from Vcc to charge a capacitor connected to the Vcap pin. This stored charge will be used by the chip to perform a single STORE operation. If the voltage on the Vcc pin drops below Vswitch, the part will automatically disconnect the Vcap pin from Vcc. A STORE operation will be initiated with power provided by the Vcap capacitor.

Figure 5 shows the proper connection of the storage capacitor (Vcap) for automatic store operation. Refer to the DC CHARACTERISTICS table for the size of Vcap. The voltage on the Vcap pin is driven to 5V by a charge pump internal to the chip. A pull up should be placed on \overline{W} to hold it inactive during power up.

To reduce unneeded nonvolatile stores, $AutoStore^{TM}$ and Hardware Store operations will be ignored unless at least one WRITE operation has taken place since the most recent STORE or RECALL cycle. Software initiated STORE cycles are performed regardless of whether a WRITE operation has taken place. The \overline{HSB} signal can be monitored by the system to detect an $AutoStore^{TM}$ cycle is in progress.

HARDWARE STORE (HSB) OPERATION

The STK17TA8 provides the $\overline{\mbox{HSB}}$ pin for controlling and acknowledging the STORE operations. The HSB pin can be used to request a hardware STORE cycle. When the $\overline{\mbox{HSB}}$ pin is driven low, the STK17TA8 will conditionally initiate a STORE operation after t_{DELAY} . An actual STORE cycle will only begin if a WRITE to the SRAM took place since the last STORE or RECALL cycle. The $\overline{\mbox{HSB}}$ pin also acts as an open drain driver that is internally driven low to indicate a busy condition while the STORE (initiated by any means) is in progress.

SRAM READ and WRITE operations that are in progress when $\overline{\mbox{HSB}}$ is driven low by any means are given time to complete before the STORE operation is initiated. After $\overline{\mbox{HSB}}$ goes low, the STK17TA8 will continue SRAM operations for t_{DELAY} . During t_{DELAY} , multiple SRAM READ operations may take place. If a WRITE is in progress when $\overline{\mbox{HSB}}$ is pulled low it will be allowed a time, t_{DELAY} , to complete. However, any SRAM WRITE cycles requested after $\overline{\mbox{HSB}}$ goes low will be inhibited until $\overline{\mbox{HSB}}$ returns high.

During any STORE operation, regardless of how it was initiated, the STK17TA8 will continue to drive the $\overline{\mbox{HSB}}$ pin low, releasing it only when the STORE is complete. Upon completion of the STORE operation the STK17TA8 will remain disabled until the $\overline{\mbox{HSB}}$ pin returns high.

If HSB is not used, it should be left unconnected.

HARDWARE RECALL (POWER-UP)

During power up, or after any low-power condition ($V_{CC} < V_{SWITCH}$), an internal *RECALL* request will be latched. When V_{CC} once again exceeds the sense voltage of V_{SWITCH} , a *RECALL* cycle will automatically be initiated and will take $t_{HRECALL}$ to complete.

SOFTWARE STORE

Data can be transferred from the SRAM to the nonvolatile memory by a software address sequence. The STK17TA8 software STORE cycle is initiated by executing sequential \overline{E} controlled READ cycles from six specific address locations in exact order. During the STORE cycle an erase of the previous nonvolatile data is first performed, followed by a program of the nonvolatile elements. Once a STORE cycle is initiated, further input and output are disabled until the cycle is completed.

Because a sequence of READs from specific addresses is used for *STORE* initiation, it is important that no other READ or WRITE accesses intervene in the sequence, or the sequence will be aborted and no *STORE* or *RECALL* will take place.

To initiate the software *STORE* cycle, the following READ sequence must be performed:

1.	Read address	0x4E38	Valid READ
2.	Read address	0xB1C7	Valid READ
3.	Read address	0x83E0	Valid READ
4.	Read address	0x7C1F	Valid READ
5.	Read address	0x703F	Valid READ
6.	Read address	0x8FC0	Initiate STORE cycle

The software sequence may be clocked with $\overline{\epsilon}$ controlled READs or $\overline{\epsilon}$ controlled READs.

Once the sixth address in the sequence has been entered, the STORE cycle will commence and the chip will be disabled. It is important that READ cycles and not WRITE cycles be used in the sequence, although it is not necessary that \overline{G} be low for the sequence to be valid. After the t_{STORE} cycle time has been fulfilled, the SRAM will again be activated for READ and WRITE operation.

SOFTWARE RECALL

Data can be transferred from the nonvolatile memory to the SRAM by a software address sequence. A software RECALL cycle is initiated with a sequence of READ operations in a manner similar to the software STORE initiation. To initiate the RECALL cycle, the following sequence of \overline{E} controlled READ operations must be performed:

1.	Read address	0x4E38	Valid READ
2.	Read address	0xB1C7	Valid READ
3.	Read address	0x83E0	Valid READ
4.	Read address	0x7C1F	Valid READ
5.	Read address	0x703F	Valid READ
6.	Read address	0x4C63	Initiate RECALL cycle

Internally, *RECALL* is a two-step procedure. First, the SRAM data is cleared, and second, the nonvolatile information is transferred into the SRAM cells. After the t_{RECALL} cycle time the SRAM will once again be ready for READ and WRITE operations. The *RECALL* operation in no way alters the data in the nonvolatile elements.

DATA PROTECTION

The STK17TA8 protects data from corruption during low-voltage conditions by inhibiting all externally initiated STORE and WRITE operations. The low-voltage condition is detected when $V_{\rm CC} < V_{\rm SWITCH}$.

If the STK17TA8 is in a WRITE mode (both $\overline{\mathbb{E}}$ and $\overline{\mathbb{W}}$ low) at power-up, after a RECALL, or after a STORE, the WRITE will be inhibited until a negative transition on $\overline{\mathbb{E}}$ or $\overline{\mathbb{W}}$ is detected. This protects against inadvertent writes during power up or brown out conditions.

NOISE CONSIDERATIONS

The STK17TA8 is a high-speed memory and so must have a high-frequency bypass capacitor of approximately $0.1\mu F$ connected between V_{CC} and V_{SS} , using leads and traces that are as short as possible. As with all high-speed CMOS ICs, careful routing of power, ground and signals will reduce circuit noise.

LOW AVERAGE ACTIVE POWER

CMOS technology provides the STK17TA8 this the benefit of drawing significantly less current when it is cycled at times longer than 50ns. Figure 6 shows the relationship between $I_{\rm CC}$ and READ/WRITE cycle time. Worst-case current consumption is shown for commercial temperature range, $V_{\rm CC}$ = 3.6V, and chip enable at maximum frequency. Only standby current is drawn when the chip is disabled. The overall average current drawn by the STK17TA8 depends on the following items:

- 1. The duty cycle of chip enable.
- 2. The overall cycle rate for accesses.
- 3. The ratio of READs to WRITEs.
- 4. The operating temperature.
- 5. The V_{CC} level.
- 6. I/O loading.

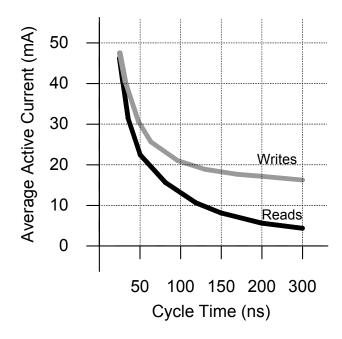


Figure 6 Current vs. Cycle time

PREVENTING AUTOSTORE TM

Because of the use of nvRAM to store critical RTC data the $AutoStore^{TM}$ function can be not be disabled in the STK17TA8 .

REAL TIME CLOCK OPERATION

nvTIME OPERATION

The STK17TA8 offers internal registers that contain Clock, Alarm, Watchdog, Interrupt, and Control functions. Internal double buffering of the clock and the clock/timer information registers prevents accessing transitional internal clock data during a read or write operation. Double buffering also circumvents disrupting normal timing counts or clock accuracy of the internal clock while accessing clock data. Clock and Alarm Registers store data in BCD format.

CLOCK OPERATIONS

The clock registers maintain time up to 9,999 years in one second increments. The user can set the time to any calendar time and the clock automatically keeps track of days of the week and month, leap years and century transitions. There are eight registers dedicated to the clock functions which are used to set time with a write cycle and to read time during a read cycle. These registers contain the Time of Day in BCD format. Bits defined as "X" are currently not used and are reserved for future use by Simtek.

READING THE CLOCK

While the double-buffered RTC register structure reduces the chance of reading incorrect data from the clock, the user should halt internal updates to the STK17TA8 clock registers before reading clock data to prevent the reading of data in transition. Stopping the internal register updates does not affect clock accuracy.

The updating process is stopped by writing a "1" to the read bit "R" (in the flags register at 0x1FFF0), and will not restart until a "0" is written to the read bit. The RTC registers can then be read while the internal clock continues to run.

Within 20ms after a "0" is written to the read bit, all STK17TA8 registers are simultaneously updated.

SETTING THE CLOCK

Setting the write bit "W" (in the flags register at 0x1FFF0) to a "1" halts updates to the STK17TA8 registers. The correct day, date and time can then be written into the registers in 24-hour BCD format. The time written is referred to as the "Base Time." This value is stored in nonvolatile registers and used in calculation of the current time. Resetting the write bit to "0" transfers those values to the actual clock counters, after which the clock resumes normal operation.

BACKUP POWER

The RTC in the STK17TA8 is intended for permanently powered operation. Either the V_{RTCcap} or V_{RTCbat} pin is connected depending on whether a capacitor or battery is chosen for the application. When primary power, V_{cc} , fails and drops below V_{switch} the device will switch to the backup power supply.

The clock oscillator uses very little current, which maximizes the backup time available from the backup source. Regardless of clock operation with the primary source removed, the data stored in nvSRAM is secure, having been stored in the nonvolatile elements as power was lost. Factors to be considered when choosing a backup power source include: the expected duration of power outages and the cost trade-off of using a battery versus a capacitor.

During backup operation the STK17TA8 consumes a maximum of 300 nanoamps at 2 volts. Capacitor or battery values should be chosen according to the application. Backup time values based on maximum current specs are shown below. Nominal times are approximately 3 times longer.

Capacitor Value	Backup Time
0.1 F	72 hours
0.47 F	14 days
1.0 F	30 days

Using a capacitor has the obvious advantage of recharging the backup source each time the system is powered up.

If a battery is used, a 3V lithium is recommended and the STK17TA8 will only source current from the battery when the primary power is removed. The battery will not, however, be recharged at any time by the STK17TA8. The battery capacity should be chosen for total anticipated cumulative down-time required over the life of the system.

STOPPING AND STARTING THE OSCIL-LATOR

The OSCEN bit in calibration register at 0x1FFF8 controls the starting and stopping of the oscillator. This bit is nonvolatile and shipped to customers in the "enabled" (set to 0) state. To preserve battery life while system is in storage OSCEN should be set to a 1. This will turn off the oscillator circuit extending the battery life. If the OSCEN bit goes from disabled to enabled, it will take approximately 5 seconds (10 seconds max) for the oscillator to start.

The STK17TA8 has the ability to detect oscillator failure. This is recorded in the OSCF (Oscillator Failed bit) of the flags register at address 0x1FFF0. When the device is powered on (V_{CC} goes above V_{switch}) the \overline{oscen} bit is checked for "enabled" status. If the \overline{oscen} bit is enabled and the oscillator is not active, the OSCF bit is set. The user should check for this condition and then write a 0 to clear the flag. It should be noted that in addition to setting the OSCF flag bit, the time registers are reset to the "Base Time" (see the section "Setting the Clock"), which is the value last written to the timekeeping registers. The Control/Calibration register and the \overline{oscen} bit are not affected by the oscillator failed condition.

If the voltage on the backup supply (either V_{RTCcap} or V_{RTCbat}) falls below their respective minimum level the oscillator may fail, leading to the oscillator failed condition which can be detected when system power is restored.

The value of OSCF should be reset to 0 when the time registers are written for the first time. This will initialize the state of this bit which may have become set when the system was first powered on.

CALIBRATING THE CLOCK

The RTC is driven by a quartz controlled oscillator with a nominal frequency of 32.768 KHz. Clock accuracy will depend on the quality of the crystal, usually specified to 35 ppm limits at 25°C. This error could equate to <u>+</u> 1.53 minutes per month. The STK17TA8 employs a calibration circuit that can improve the accuracy to +1/-2 ppm at 25°C. The

calibration circuit adds or subtracts counts from the oscillator divider circuit.

The number of times pulses are suppressed (subtracted, negative calibration) or split (added, positive calibration) depends upon the value loaded into the five calibration bits found in calibration register at 0x1FFF8. Adding counts speeds the clock up; subtracting counts slows the clock down. The Calibration bits occupy the five lower order bits in the control register 8. These bits can be set to represent any value between 0 and 31 in binary form. Bit D5 is a Sign bit, where a "1" indicates positive calibration and a "0" indicates negative calibration. Calibration occurs within a 64 minute cycle. The first 62 minutes in the cycle may, once per minute, have one second either shortened by 128 or lengthened by 256 oscillator cycles.

If a binary "1" is loaded into the register, only the first 2 minutes of the 64 minute cycle will be modified; if a binary 6 is loaded, the first 12 will be affected, and so on. Therefore each calibration step has the effect of adding 512 or subtracting 256 oscillator cycles for every 125,829,120 actual oscillator cycles. That is +4.068 or -2.034 ppm of adjustment per calibration step in the calibration register.

In order to determine how to set the calibration one may set the CAL bit in the flags register at 0x1FFF0 to 1, which causes the INT pin to toggle at a nominal 512 Hz. Any deviation measured from the 512 Hz will indicate the degree and direction of the required correction. For example, a reading of 512.010124 Hz would indicate a +20 ppm error, requiring a -10 (001010) to be loaded into the Calibration register. Note that setting or changing the calibration register does not affect the frequency test output frequency.

ALARM

The alarm function compares user-programmed values to the corresponding time-of-day values. When a match occurs, the alarm event occurs. The alarm drives an internal flag, AF, and may drive the INT pin if desired.

There are four alarm match fields. They are date, hours, minutes and seconds. Each of these fields also has a Match bit that is used to determine if the field is used in the alarm match logic. Setting the Match bit to "0" indicates that the corresponding field will be used in the match process.

Depending on the Match bits, the alarm can occur as specifically as one particular second on one day of the month, or as frequently as once per second continuously. The MSB of each alarm register is a Match bit. Selecting none of the Match bits (all 1's) indicates that no match is required. The alarm occurs every second. Setting the match select bit for seconds to "0" causes the logic to match the seconds alarm value to the current time of day. Since a match will occur for only one value per minute, the alarm occurs once per minute. Likewise, setting the seconds and minutes Match bits causes an exact match of these values. Thus, an alarm will occur once per hour. Setting seconds, minutes and hours causes a match once per day. Lastly, selecting all match values causes an exact time and date match. Selecting other bit combinations will not produce meaningful results; however the alarm circuit should follow the functions described.

There are two ways a user can detect an alarm event, by reading the AF flag or monitoring the INT pin. The AF flag in the flags register at 0x1FFF0 will indicate that a date/time match has occurred. The AF bit will be set to 1 when a match occurs. Reading the Flags/Control register clears the alarm flag bit (and all others). A hardware interrupt pin may also be used to detect an alarm event.

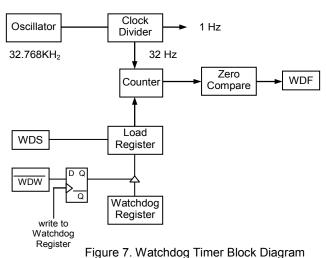
WATCHDOG TIMER

The watchdog timer is a free running down counter that uses the 32 Hz clock (31.25 ms) derived from the crystal oscillator. The oscillator must be running for the watchdog to function. It begins counting down from the value loaded in the Watchdog Timer register.

The counter consists of a loadable register and a free running counter. On power up, the watchdog time-out value in register 0x1FFF7 is loaded into the counter load register. Counting begins on power up and restarts from the loadable value any time the Watchdog Strobe (WDS) bit is set to 1. The counter is compared to the terminal value of 0. If the counter reaches this value, it causes an internal flag and an optional interrupt output. The user can prevent the time-out interrupt by setting WDS bit to 1 prior to the counter reaching 0. This causes the counter to be reloaded with the watchdog time-out value and to be restarted. As long as the user sets the WDS bit prior to the counter reaching the terminal value, the interrupt and flag never occurs.

New time-out values can be written by setting the watchdog write bit to 0. When the $\overline{\text{wow}}$ is 0 (from the previous operation), new writes to the watchdog time-out value bits D_5 - D_0 allow the time-out value to be modified. When $\overline{\text{wow}}$ is a 1, then writes to bits D_5 - D_0 will be ignored. The $\overline{\text{wow}}$ function allows a user to

set the WDS bit without concern that the watchdog timer value will be modified. A logical diagram of the watchdog timer is shown below. Note that setting the watchdog time-out value to 0 would be otherwise meaningless and therefore disables the watchdog function.



The output of the watchdog timer is a flag bit WDF that is set if the watchdog is allowed to time-out. The flag is set upon a watchdog time-out and cleared when the Flags/Control register is read by the user. The user can also enable an optional interrupt source to drive the INT pin if the watchdog time-out occurs.

POWER MONITOR

The STK17TA8 provides a power management scheme with power-fail interrupt capability. It also controls the internal switch to backup power for the clock and protects the memory from low- $V_{\rm CC}$ access. The power monitor is based on an internal band-gap reference circuit that compares the $V_{\rm CC}$ voltage to various thresholds.

As described in the $AutoStore^{\intercal M}$ section previously, when V_{switch} is reached as V_{CC} decays from power loss, a data store operation is initiated from SRAM to the nonvolatile elements, securing the last SRAM data state. Power is also switched from V_{CC} to the backup supply (battery or capacitor) to operate the RTC oscillator.

When operating from the backup source no data may be read or written and the clock functions are not available to the user. The clock continues to operate in the background. Updated clock data is available to the user after $t_{HRECALL}$ delay (See *AutoStore*TM /POWER-UP *RECALL*) after V_{CC} has been restored to the device.

INTERRUPTS

The STK17TA8 provides three potential interrupt sources. They include the watchdog timer, the power monitor, and the clock/calendar alarm. Each can be individually enabled and assigned to drive the INT pin. In addition, each has an associated flag bit that the host processor can use to determine the cause of the interrupt.

Some of the sources have additional control bits that determine functional behavior. In addition, the pin driver has three bits that specify its behavior when an interrupt occurs. A functional diagram of the interrupt logic is shown below.

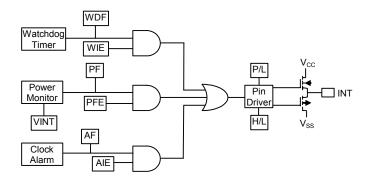


Figure 8. Interrupt Block Diagram

The three interrupts each have a source and an enable. Both the source and the enable must be active (true high) in order to generate an interrupt output. Only one source is necessary to drive the pin. The user can identify the source by reading the Flags/Control register, which contains the flags associated with each source. All flags are cleared to 0 when the register is read. The cycle must be a complete read cycle ($\overline{\text{WE}}$ high); otherwise the flags will not be cleared. The power monitor has two programmable settings that are explained in the power monitor section.

Once an interrupt source is active, the pin driver determines the behavior of the output. It has two programmable settings as shown below. Pin driver control bits are located in the Interrupts register.

According to the programming selections, the pin can be driven in the backup mode for an alarm interrupt. In addition, the pin can be an active low (open-drain) or an active high (push-pull) driver. If programmed for operation during backup mode, it can only be active low. Lastly, the pin can provide a one-shot function so that the active condition is a pulse or a level condition. In one-shot mode, the pulse width is internally fixed at approximately 200 ms. This mode is intended to reset a host microcontroller. In level mode, the pin goes to its active polarity until the Flags/Control register is read by the user. This mode is intended to be used as an interrupt to a host microcontroller. The control bits are summarized as follows:

Watchdog Interrupt Enable - WIE. When set to 1, the watchdog timer drives the INT pin as well as an internal flag when a watchdog time-out occurs. When WIE is set to 0, the watchdog timer affects only the internal flag.

Alarm Interrupt Enable - AIE. When set to 1, the alarm match drives the INT pin as well as an internal flag. When set to 0, the alarm match only affects to internal flag.

Power Fail Interrupt Enable - PFE. When set to 1, the power fail monitor drives the pin as well as an internal flag. When set to 0, the power fail monitor affects only the internal flag.

High/Low - H/L. When set to a 1, the INT pin is active high and the driver mode is push-pull. The INT pin can drive high only when $V_{\rm CC} > V_{\rm switch}$. When set to a 0, the INT pin is active low and the drive mode is opendrain. Active low (open drain) is operational even in battery backup mode.

Pulse/Level - P/L. When set to a 1 and an interrupt occurs, the INT pin is driven for approximately 200 ms. When P/L is set to a 0, the INT pin is driven high or low (determined by H/L) until the Flags/Control register is read.

When an enabled interrupt source activates the INT pin, an external host can read the Flags/Control register to determine the cause. Remember that all flags will be cleared when the register is read. If the INT pin is programmed for Level mode, then the condition will clear and the INT pin will return to its inactive state. If the pin is programmed for Pulse mode, then reading the flag also will clear the flag and the pin. The pulse will not complete its specified duration if the Flags/Control register is read. If the INT pin is used as a host reset, then the Flags/Control register should not be read during a reset.

During a power-on reset with no battery, the interrupt register is automatically loaded with the value 24h. This causes power-fail interrupt to be enabled with an active-low pulse.

RTC Register Map

Dominton			Е	CD Form	at Data				Function / Bonne
Register	D7	D6	D5	D4	D3	D2	D1	D0	Function / Range
0x1FFFF		10s Ye	ars			Yea	rs		Years: 00-99
0x1FFFE	0	0	0	10s Months		Mont	hs		Months: 01-12
0x1FFFD	0	0		Day of onth		Day of I	Month		Day of Month: 01-31
0x1FFFC	0	0	0	0	0	Da	y of W	eek	Day of week: 01-07
0x1FFFB	0	0	10s	Hours		Hou	rs		Hours: 00-23
0x1FFFA	0	10	s Minut	es		Minu	tes		Minutes: 00-59
0x1FFF9		10	s Secor	nds		Secoi	nds		Seconds: 00-59
0x1FFF8	OSCEN	0	Cal Sign		Ca	libration			Calibration values*
0x1FFF7	WDS	WDW			WD	Т			Watchdog*
0x1FFF6	WIE	AIE	PFE	ABE	H/L	P/L	0	0	Interrupts*
0x1FFF5	M	0		Alarm Date		Alarm	Day		Alarm, Day of Month: 01-31
0x1FFF4	M	0		10s Alarm Hours Alarm Hours			Alarm, hours: 00-23		
0x1FFF3	M	10 A	larm Mir	nutes		Alarm M	inutes	_	Alarm, minutes: 00-59
0x1FFF2	M	10 AI	arm Sed	conds		Alarm Se	conds		Alarm, seconds: 00-59
0x1FFF1		10s Cent	turies			Centu	ries		Centuries: 00-99
0x1FFF0	WDF	AF	PF	OSCF	0	CAL	W	R	Flags*

^{* -} Is a binary value, not a BCD value.0 - Not implemented, reserved for future use.

Register Map Detail

0x1FFFF					eping – Ye								
XIFFFF	D7	D6	D5	D4	D3	D2	D1	D0					
			Years				Years						
								for years; upper					
	register		alue for 10s	or years. Eac	on nibble op	erates from	U to 9. In	e range for the					
	register	15 0-99.											
	Timekeeping – Months												
x1FFFE	D7	D6	D5	D4	D3	D2	D1	D0					
	0	0	0	10s Month			Months						
			,		nibble conta	ins the lowe		operates from 0					
								range for the					
	register		,	• • •									
				Timek	eeping – D	ate							
)x1FFFD	D7	D6	D5	D4	D3	D2	D1	D0					
	0	0	10s Day	of month		Day	of month	1					
			gits for the d	ate of the mo		nibble conta	ins the lov	wer digit and					
							es from 0	to 3. The range for					
	the regis	ter is 1-31. L	₋eap years a	re automatic	ally adjuste	d for.							
x1FFFC					eeping – D		I						
XIIIIC	D7	D6	D5	D4	D3	D2	D1	D0					
	0	0	0	0	0		Day of						
								ek is a ring counte					
					user must a	ssign meani	ng to the o	day value, as the					
	uay is no	ot integrated	with the date	.									
		-		Timeke	eping – Ho	uro							
x1FFFB	D7	D6	D5	D4	D3	D2	D1	D0					
	12/24	0			D3	DZ		D0					
		-		Hours	rmat Lowe	r nibble con	Hours	ower digit and					
								es from 0 to 2. Th					
				c (two bito) o	oritaino trio	apper aight c	па орога	00 110111 0 10 2. 11					
	range for the register is 0-23.												
				Timekee	ping – Min	utes							
0x1FFFA	D7	D6	D5	D4	D3	D2	D1	D0					
	0		10s Minutes	S		•	Minutes	•					
	Contains	the BCD va			ble contain			perates from 0 to					
	Contains the BCD value of minutes. Lower nibble contains the lower digit and operates from 0 to 9 upper nibble contains the upper minutes digit and operates from 0 to 5. The range for the register												
	upper ni	bble contains	s the upper i	is 0-59.									
		bble contain:	s trie upper i	minutes digit									
		bble contain:	s the upper i	Timates digit									
	is 0-59.	bble contain:	s trie upper r		ping – Sec	onds							
)x1FFF9		D6	D5		ping – Sec	onds D2	D1	D0					
0x1FFF9	is 0-59.		D5	Timekee D4		D2	D1 Seconds	D0					
0x1FFF9	D7 0 Contains	D6 s the BCD va	D5 10s Second	Timekee D4 s nds. Lower ni	D3 bble contair	D2	Seconds digit and o	operates from 0 to					
0x1FFF9	D7 0 Contains	D6 s the BCD va	D5 10s Second	Timekee D4 s nds. Lower ni	D3 bble contair	D2	Seconds digit and o	D0 operates from 0 to the register is 0-					

WDT

	Calibration / Control									
0x1FFF8	D7	D6	D5	D4	D3	D2	D1	D0		
	OSCEN	0	Calibration Sign			Calibra	ation			
OSCEN	Oscillator Enable. When set to 1, the oscillator is halted. When set to 0, the oscillator runs. Disabling the oscillator saves battery/capacitor power during storage. On a no-battery power-up, this bit is set to 0.									
Calibration Sign	Determines time-base.	s if the calibr	ration adjustm	ent is applie	ed as an ac	ldition to or	as a subtrac	tion from the		
Calibration These five bits control the calibration of the clock.										
Calibration	These live	DIES CONTROL	ine calibration	of the cloc	ζ.					
	These live	DIES CONTION	the calibration		dog Timer					
	D7	D6	D5			D2	D1	D0		
Calibration 0x1FFF7				Watch	dog Timer		D1	D0		
	D7 WDS Watchdog has no affe	D6 WDW Strobe. Settect. The bit is	D5	Watche D4 1 reloads as matically or	dog Timer D3	D2 WDT the watchdo	og timer. Set	tting the bit to (

This function is explained in more detail in the watchdog timer section.

was cleared to 0 on a previous cycle.

The new value will be loaded on the next internal watchdog clock after the write cycle is complete.

value is 31.25 ms (a setting of 1) and the maximum time-out is 2 seconds (setting of 3Fh). Setting the watchdog timer register to 0 disables the timer. These bits can be written only if the WDW bit

Watchdog time-out selection. The watchdog timer interval is selected by the 6-bit value in this register. It represents a multiplier of the 32 Hz count (31.25 ms). The minimum range or time-out

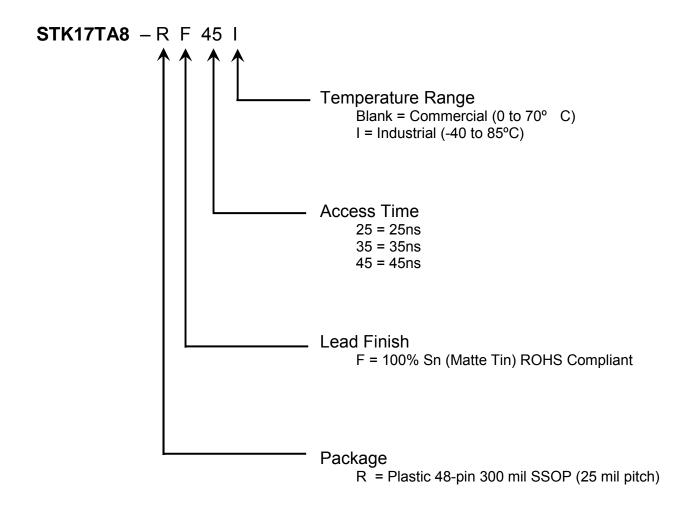
	Interrupt Status / Control										
0x1FFF6	D7	D6	D5	D4	D3	D2	D1	D0			
	WIE	AIE	PFIE	ABE	H/L	P/L	0	0			
WIE	Watchdog Interrupt Enable. When set to 1 and a watchdog time-out occurs, the watchdog timer drives the INT pin as well as the WDF flag. When set to 0, the watchdog time-out affects only the WDF flag.										
AIE		•		to 1, the ala		Irives the IN	Γ pin as well	as the AF flag.			
PFIE				, the alarm nects only the		s the INT pin	as well as t	he AF flag. When			
ABE								AIE) will function			
H/L	even in battery backup mode. When set to 0, the alarm will occur only when V _{cc} >V _{switch} . High/Low. When set to a 1, the INT pin is driven active high. When set to 0, the INT pin is open drain, active low.										
	Pulse/Leve	l. When se	to a 1, the	INT pin is dr	ven active	(determined	by H/L) b	y an interrupt			
P/L	source for	approximat	ely 200 ms.	When set to	a 0, the IN	IT pin is drive	en to an activ	ve level (as set			
	by H/L)	until the Fla	gs/Control	register is rea	ad.						

				Ala	rm – Day						
0x1FFF5	D7	D6	D5	D4	D3	D2	D1	D0			
	M	0	10s Ala	10s Alarm Date Alarm Date							
	Contains	ı s the alarm v	l /alue for the	date of the m	ı onth and th	e mask bit t	o select or c	leselect the date			
	value.										
M				es the date values the date value in the date value in the date value in the date value in the second in the secon		ed in the ala	arm match. S	Setting this bit to 1			
				Λlar	m – Hours						
0x1FFF4	D7	D6	D5	D4	D3	D2	D1	D0			
	M	0	10s Ala	ırm Hours		Al	arm Hours				
				hours and the							
M	Match. Setting this bit to 0 causes the hours value to be used in the alarm match. Setting this bit to 1 causes the match circuit to ignore the hours value.										
				Alorn	n – Minutes						
0x1FFF3	D7	D6	D5	D4	D3	D2	D1	D0			
	M	10	s Alarm Min	utes		Ala	ırm Minutes				
		Contains the alarm value for the minutes and the mask bit to select or deselect the minutes value.									
M				es the minutes gnore the min		used in the	alarm mato	ch. Setting this bit			
	_										
0x1FFF2				Alarn	n – Second	s					
UXIFFF2	D7	D6	D5	D4	D3	D2	D1	D0			
	M	10:	s Alarm Sec	onds	Alarm Seconds						
	Contains the alarm value for the seconds and the mask bit to select or deselect the seconds' value.										
M	Match. S			es the seconds to ignore the s			e alarm mat	ch. Setting this			
0x1FFF1					oing – Cent						
	D7	D6	D5	D4	D3	D2	D1	D0			
	0	_	0 10s Centuries Centuries								

STK17TA8

	Flags											
0x1FFF0	D7	D6	D5	D4	D3	D2	D1	D0				
	WDF	AF	PF	OSCF	0	CAL	W	R				
WDF	Watchdog Timer Flag. This read-only bit is set to 1 when the watchdog timer is allowed to reach 0 without being reset by the user. It is cleared to 0 when the Flags/Control register is read.											
AF				et to 1 when s = 0. It is cle				s stored in the er is read.				
PF				is set to 1 w Flags/Contro			he power-fai	il threshold				
OSCF	power-on o	peration.	This indicate	ower-up only es that time of e chip will not	ounts are r	no longer val	id. The user	r must reset this				
CAL			,					When set to 0, up.				
W	the INT pin resumes normal operation. This bit defaults to 0 (disabled) on power up. Write Time. Setting the W bit to 1 freeze updates of the timekeeping registers. The user can then write them with updated values. Setting the W bit to 0 causes the contents of the time registers to be transferred to the timekeeping counters.											
R	them in a h	olding registem errors	ster. The us	er can then r going from 0	ead them v	without conce	erns over ch	rs and places anging values e, so the bit must				

ORDERING INFORMATION



Document Revision History

Revision	Date	Summary							
0.0	February 2003	Publish new datasheet							
0.1	March 2003	Remove 525 mil SOIC, Add 48 Pin SSOP and 40 Pin DIP packages; Modified Block Diagram in <i>AutoStore</i> description section Modify 600 mil DIP pin-out (switch pins 32 and 33), Update Power-up Recall specs,							
0.2	June 2003	Modify 600 mil DIP pin- Update Software Contro Modified Mode Selectio	olled Store/Recall Cy	cle, Added Hardware	Store Description,				
0.3	February 2004	Change part number fro	om STK17CA8 to ST	K17TA8; Add lead-fre	e finish option				
		Parameter	Old Value	New Value	Notes				
		Vcap Min	10μF	17 μF					
		t _{VCCRISE}	NA	150 µs	New Spec				
		I _{CC1} Max Com.	35 mA	50 mA	@ 45ns access				
		I _{CC1} Max Com.	40 mA	55 mA	@ 35ns access				
		I _{CC1} Max Com.	50 mA	65 mA	@ 25ns access				
		I _{CC1} Max Ind.	35 mA	55 mA	@ 45ns access				
		I _{CC1} Max Ind.	45 mA	60 mA	@ 35ns access				
1.0	December 2004	I _{CC1} Max Ind.	55 mA	70 mA	@ 25ns access				
		I _{CC2} Max	1.5 mA	3.0 mA	Com. & Ind.				
		I _{CC4} Max	0.5 mA	3 mA	Com & Ind.				
		t _{HRECALL}	5 ms	20 ms					
		t _{STORE}	10 ms	12.5 ms					
		t _{RECALL}	20 μs	40 μs					
		t _{GLQV}	10 ns	12 ns	@ 25 ns access				
1.1	April 2005	Changed RTC register	r unused bits "X" to re	equire zero "0" value v	when writing values.				
	<u> </u>	Parameter	Old Value	New Value	Notes				
		I _{CC3} Max Com.	5 mA	10 mA					
		I _{CC3} Max Ind.	5 mA	10 mA					
		I _{SB} Max Com.	3 mA	3 mA					
		I _{SB} Max Ind.	3 mA	3 mA					
		t _{RECALL}	40 µs	50 µs	Soft Recall				
		t _{STORE}	12.5 ms	15 ms	Industrial Grade Only				
1.2	September 2005	Max. STORE Cycles	1x10 ⁶	5x10 ⁵	Contact Simtek for details.				
		t _{oscs}	1 min	10 sec	@ MIN Temperature				
		t _{oscs}	10 sec	5 sec	@ 25°C from Power up				
			00 5	0.5					
		C_1	2.2 pF	0 pF	RTC Output Cap				
		C_1 C_2	2.2 pF 47 pF	56 pF	RTC Output Ca				

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